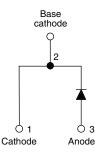
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 30 A



www.vishay.com



PRIMARY CHARACTERISTICS				
I _{F(AV)}	30 A			
V _R	1200 V			
V _F at I _F	2.3 V			
t _{rr} typ.	47 ns			
T _J max.	150 °C			
Package	TO-247AC 2L			
Circuit configuration	Single			

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to ${\sf JEDEC}^{\circledast}\text{-}{\sf JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA30PB120... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 30 A continuous current, the VS-HFA30PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		1200	V		
Maximum continuous forward current	١ _F	T _C = 100 °C	30			
Single pulse forward current	I _{FSM}	t _p = 10 ms	120	А		
Maximum repetitive forward current	I _{FRM}		90			
Maximum power dissipation	P _D	T _C = 25 °C	350	W		
Maximum power dissipation		T _C = 100 °C	140	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		

RoHS COMPLIANT HALOGEN FREE

Revision: 29-Nov-2019

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-	
		I _F = 30 A		-	2.4	4.1	v
Maximum forward voltage V _{FM}	I _F = 60 A	See fig. 1	-	3.1	5.7		
		I _F = 30 A, T _J = 125 °C		-	2.3	4.0	
Maximum reverse		$V_R = V_R$ rated	See fig. 0	-	1.3	40	
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	1100	4000	μA
Junction capacitance	CT	V _R = 200 V See fig. 3		-	50	75	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 - nl				nH	

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	47	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	110	170	ns
000 lig. 0, 10	t _{rr2}	T _J = 125 °C	C - 170	170	260		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	10	15	A
See fig. 6	I _{RRM2}	T _J = 125 °C	I _F = 30 A	-	16	24	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dl _F /dt = 200 A/µs	-	650	980	nC
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	1540	2310	no
Peak rate of fall of recovery	dl _{(rec)M} /dt1	T _J = 25 °C]	-	270	-	A/µs
current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	240	-	Αγμδ

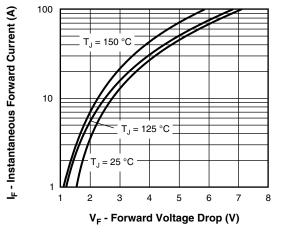
THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	0.36	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.50	-	
Weight			-	5.61	-	g
weight			-	0.198	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC 2L	HFA30PB120			

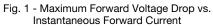
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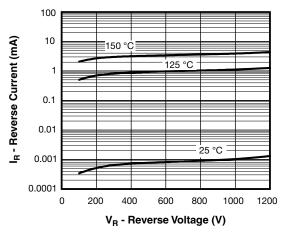


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

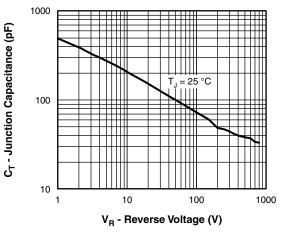


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

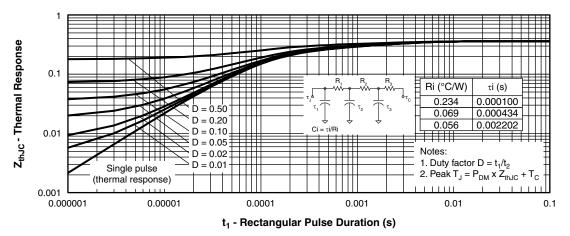


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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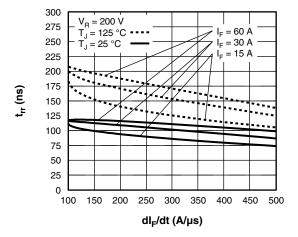


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

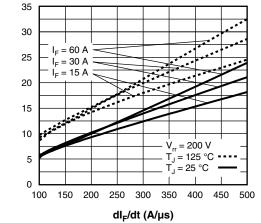
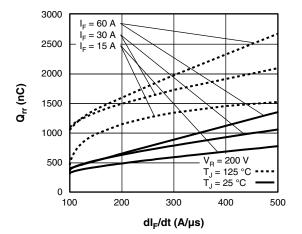


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)



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Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

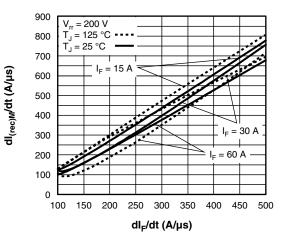


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

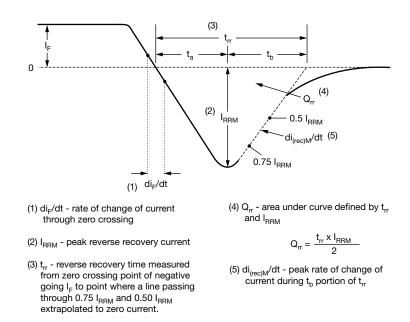


Fig. 9 - Reverse Recovery Waveform and Definitions

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I_{RRM} (A)



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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	30	РВ	120	-N3
		2	3	4	5	6	7
	1 - 2 - 3 - 4 - 5 - 6 - 7 -	HE: Electric Cur B Voltric Env	XFRED [®] ctron irra rent rati = TO-24 age rati ironmer	-	= 30 A) pins) = 1200) V)	

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA30PB120-N3	25	500	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96144			
Part marking information www.vishay.com/doc?95648				



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